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SHEET 1 OF 1

**INFORMATION DISCLOSURE  
CITATION IN AN  
APPLICATION**

(PTO-1449)

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**APPLICANT**  
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2818

# U.S. PATENT DOCUMENTS

**FOREIGN PATENT DOCUMENTS**

(including Authors, Title, Date, Refereed, Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.'
<i>by</i>		"A Precise On-Chip Voltage Generator for a Gigascale DRAM with a Negative Word-Line Scheme", by Tanaka et al., IEEE Journal of Solid-State Circuits, Vol. 34, No. 8, 8/1999, pp. 1084-1090.
<i>by</i>		"Ultra LSI Memory" by Kiyoo Ito, Advanced Electronics Series, November 5, 1994, published by Baifukan, pp. 351-371.
<i>by</i>		"An Experimental 256-Mb DRAM with Boosted Sense-Ground Scheme", by Asakura et al., IEEE Journal of Solid-State Circuits, Vol. 29, No. 11, 11/1994, pp. 1303-1309.
<i>C</i>		

**EXAMINER**

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**1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.**